

IN THE CLAIMS:

Please cancel Claims 7 and 14 without prejudice.

Please amend Claims 1, 8, and 9 by rewriting the same as follows:

1. ~~(Amended)~~ A damascene interconnection comprising:
an interconnection trench formed in an insulating film and a pad trench communicating therewith;
a protrusion formed by a portion not removed of said insulating film in said pad trench to decrease a substantial opening area of said pad trench;
a conductive film buried in said interconnection trench and said pad trench;
and
a contact hole formed within said pad trench to electrically connect said conductive film to a further conductive film formed below said insulating film, wherein said contact hole and said further conductive film substantially suppress an increase in electrical resistance in said pad trench due to formation of said protrusion.

8. ~~(Amended)~~ A semiconductor device, comprising:
a semiconductor substrate;
an insulating film formed on said semiconductor substrate;
an interconnection trench formed on said insulating film and communicating with a semiconductor element;
a pad trench formed on said insulating film and communicating with said interconnection trench;
a protrusion formed by a portion of not removed of said insulating film in said pad trench and reducing a substantial opening area of said pad trench;
a conductive film buried in said interconnection trench and said pad trench;
a further conductive film formed below said insulating film; and